

Alexander Ermachikhin

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4219629/publications.pdf>

Version: 2024-02-01

42
papers

77
citations

1683354

5
h-index

1719596

7
g-index

42
all docs

42
docs citations

42
times ranked

69
citing authors

#	ARTICLE	IF	CITATIONS
1	A Setup for Measuring the Spectral Dispersion of External Quantum Efficiency. Instruments and Experimental Techniques, 2022, 65, 123-127.	0.1	0
2	Temperature activated conductivity of Ge ₂ Sb ₂ Te ₅ : connection to the variation of Fermi level and implications on resistance drift. Journal Physics D: Applied Physics, 2021, 54, 315302.	1.3	6
3	Investigation of the properties of zinc oxide based heterostructures. Physics of Complex Systems, 2021, 2, 172-179.	0.2	0
4	Investigation of HIT solar cells low frequency noise characteristics. Journal of Physics: Conference Series, 2021, 2103, 012105.	0.3	0
5	Influence of deep level defects on photoelectrical processes in p-n junction solar cells with porous silicon antireflection coating. , 2020, , .		1
6	Investigation of recombination centers in the active layers of HIT solar cells. , 2020, , .		0
7	External Quantum Efficiency of Bifacial HIT Solar Cells. Semiconductors, 2020, 54, 1254-1259.	0.2	3
8	Structural Dependent Eu ³⁺ Luminescence, Photoelectric and Hysteresis Effects in Porous Strontium Titanate. Materials, 2020, 13, 5767.	1.3	8
9	Kinetics of volume and surface driven crystallization in thin films. Journal of Physics Condensed Matter, 2020, 32, 355401.	0.7	3
10	Deep-Level Defects in a Photovoltaic Converter with an Antireflection Porous Silicon Film Formed by Chemical Stain Etching. Technical Physics Letters, 2019, 45, 145-148.	0.2	1
11	Current Transmission Mechanisms in the Semiconductor Structure of a Photoelectric Transducer with an n+â€“p Junction and an Antireflection Porous Silicon Film Formed by Color Etching. Technical Physics, 2019, 64, 686-692.	0.2	0
12	RESEARCH OF CHARGE TRANSFER MECHANISMS IN METAL-ZnO-SILICON HETEROSTRUCTURES. Vestnik of Ryazan State Radio Engineering University, 2019, 70, 179-189.	0.0	1
13	Mechanisms of Current Flow in the Diode Structure with an n + â€“p-Junction Formed by Thermal Diffusion of Phosphorus From Porous Silicon Film. Russian Physics Journal, 2018, 60, 1565-1571.	0.2	2
14	Application of Adaptive Algorithms for Measuring Temperature Current-Voltage Characteristics of Electronic Elements. , 2018, , .		0
15	Measurement complex on the basis of AFM for investigating charge carrier distribution in semiconductor barrier structures. , 2018, , .		0
16	Investigating and modeling high frequency C-V characteristics of zinc oxide-based heterostructures. , 2018, , .		0
17	Spatial localization of dominating deep centers in multicrystalline silicon solar cells. , 2018, , .		0
18	Measurement complex of photoluminescence using LabVIEW. , 2018, , .		0

#	ARTICLE	IF	CITATIONS
19	An Automated Measuring System for Current Deep-Level Transient Spectroscopy. Instruments and Experimental Techniques, 2018, 61, 277-282.	0.1	4
20	Excess noise and deep level defects diagnostics in semiconductor barrier structures. , 2018, , .		0
21	Investigation of Au/ZnO/Si MIS structures by capacitance-voltage characteristics method. , 2018, , .		0
22	Study of Current Flow Mechanisms in a CdS/por-Si/p-Si Heterostructure. Semiconductors, 2018, 52, 891-896.	0.2	0
23	Study of Deep Levels in a HIT Solar Cell. Semiconductors, 2018, 52, 926-930.	0.2	3
24	Investigation of electrophysical characteristics of organic solar cells based on P3HT:PEDOT blend. , 2017, , .		0
25	Investigation of recombination processes in multicrystalline silicon solar cells. , 2017, , .		1
26	Local investigation of capacitance-voltage characteristics of silicon solar cell with the modified surface. , 2017, , .		1
27	Investigation of $(\text{Ge}_{x_2}\text{Sb}_{x_2}\text{Te}_{x_5})_{1-x}\text{Bi}_x$ thin films by low frequency noise spectroscopy. , 2017, , .		0
28	Investigation of band diagram features of the DUWELL-structure InAs/InGaAs/GaAs by DLTS and low-frequency noise spectroscopy. , 2017, , .		0
29	Investigation and simulation of voltage-noise characteristics of semiconductor barrier structures. , 2017, , .		1
30	Measurement complex to investigate electrophysical and noise characteristics of semiconductor micro- and nanostructures. , 2017, , .		2
31	An analytical solution for the Fermi level of the non-degenerate semiconductor in thermal equilibrium over a wide temperature range. , 2017, , .		1
32	Defects with deep levels in a semiconductor structure of a photoelectric converter of solar energy with an antireflection film of porous silicon. Technical Physics Letters, 2017, 43, 955-957.	0.2	3
33	Investigation of Deep-Level Defects Lateral Distribution in Active Layers of Multicrystalline Silicon Solar Cells. MRS Advances, 2017, 2, 3141-3146.	0.5	1
34	An investigation of current-flow mechanisms in thin rubrene wafers prepared by the vapor transport method. Technical Physics Letters, 2016, 42, 1107-1109.	0.2	0
35	Specific features of current flow mechanisms in the semiconductor structure of a photoelectric converter with an n ⁺ -p-junction and an antireflective porous silicon film. Technical Physics, 2016, 61, 1694-1697.	0.2	4
36	Investigation of the Influence of Deep-Level Defects on the Conversion Efficiency of Sibased Solar Cells. MRS Advances, 2016, 1, 911-916.	0.5	5

#	ARTICLE	IF	CITATIONS
37	Low-resistance and high-resistance states in strontium titanate films formed by the sol-gel method. <i>Physics of the Solid State</i> , 2015, 57, 2030-2033.	0.2	3
38	The measuring systems of semiconductor structures and its software. , 2015, , .		8
39	Complex Method of Diagnostics of Diode-Like Quantum Well Heterostructures with Use of Low Frequency Noise Spectroscopy. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2015, 9, 756-761.	0.1	6
40	Apparatus for determining parameters of semiconductor structures by magnetic quantum effects and admittance spectroscopy. <i>Instruments and Experimental Techniques</i> , 2014, 57, 479-487.	0.1	1
41	Analysis of the electrostatic interaction of charges in multiple InGaAs/GaAs quantum wells by admittance-spectroscopy methods. <i>Semiconductors</i> , 2014, 48, 917-923.	0.2	6
42	A measuring System for the Spectroscopy of the Low-Frequency Noise of Semiconductor Diode Structures. <i>Measurement Techniques</i> , 2013, 56, 1066-1071.	0.2	2